

NPN SILICON SIGNAL HIGH CURRENT GENERAL PURPOSE AMPLIFIERS AND SWITCHES TO-18 PACKAGE

Type	h_{FE} @ 2V, 2mA	V_{CE0} @ 10mA Min. (V)	$V_{CE(sat)}$ @ 50mA, 50mA Max. (V)	P_T $T_A=25^\circ C$ (mW)	C_{cb} @ 10V Typical (pF)	f_t Typical (MHz)	PNP COMPLE- MENT	Comments	Package Outline No.	Specifi- cation Sheet No.			
2N5810	60-200 ⁵	25				150	2N5811	Excellent beta holdup of wide range of collector currents. Heatsinked versions ² and complementary PNP's available. Excellent as audio drivers and outputs.	175	40.88			
2N5812	150-500 ⁶					165	2N5813						
2N5814	60-120	40	.75	500 ^{1,2}	9.4	150	2N5815						
2N5816	100-200					165	2N5817						
2N5818	150-300	60				180	2N5819						
2N5820	60-120					150	2N5821						
2N5822	100-200					165	2N5823					40.90	
2N6010	100-300 ³	40		500 ^{1,2}	9.4	150	2N6011				General purpose device designed primarily for high level linear amplifiers, medium speed switching and control applications. Excellent beta linearity up to 800mA. Heatsink versions and complements available.	175	40.97
2N6012	250-500 ³					180	2N6013						
2N6014	100-300 ³	.250 ⁴	150	2N6015									
2N6016	250-500 ³	60	180	2N6017									

¹ P_T at $T_C=25^\circ C$, 1000mW

² All units available with heatsink which raises P_T to 700mW, $T_A=25^\circ C$; to specify a heatsink, substitute "HS" for "2N" in part no. Example: 2N5810 with heatsink is an HS5810. See page 20.

³ h_{FE} measured at $V_{CE}=1V$, $I_C=10mA$

⁴ $V_{CE(sat)}$ measured at $I_C=300mA$, $I_B=30mA$

⁵ 45 min h_{FE} @ $V_{CE}=2V$, $I_C=500mA$

⁶ 60 min h_{FE} @ $V_{CE}=2V$, $I_C=500mA$

PNP SILICON SIGNAL GENERAL PURPOSE SMALL SIGNAL AMPLIFIERS AND SWITCHES TO-18 PACKAGE

Type	h_{FE} @ -1V -10mA	V_{CE0} @ -10mA Min. (V)	$V_{CE(sat)}$ @ -10mA -1mA Max. (V)	P_T $T_A=25^\circ C$ (mW)	C_{cb} @ -10V 1MHz Max. (pF)	f_t Typical (MHz)	Comments	Package Outline No.	Specifi- cation Sheet No.
2N6001	100-300	-25				340	Ideal for general purpose amplifiers, high speed switching, and low noise applications. Excellent beta linearity from 10uA to 300 mA as well as guaranteed NF and switching times. NPN complements available as 2N6000, 2N6002, 2N6004, 2N6006.	175	40.94
2N6003	230-500		-100	400	8.0	400			
2N6005	100-300	-40				340			
2N6007	250-500					400			
GET3638	20 min ¹	-25V	-250 ²	400	8.0	150	Epoxy replacements for 2N3638 and 2N3638A. General purpose amplifier and medium speed switch.	175	41.22
GET3638A	100 min ¹								

¹ h_{FE} @ $V_{CE}=-10V$, $I_C=-10mA$

² $V_{CE(sat)}$ @ $I_C=-50mA$, $I_B=-2.5mA$

PNP SILICON SIGNAL HIGH SPEED SWITCHES TO-18 PACKAGE

Type	h_{FE} @ -10V -150mA	V_{CE0} @ -10mA Min. (V)	$V_{CE(sat)}$ @ -150mA -15mA Max. (V)	P_T $T_A=25^\circ C$ (mW)	C_{cb} @ -10V 1MHz Max. (pF)	f_t Typical (MHz)	t_{on} MAX (nsec)	t_{off} MAX (nsec)	Comments	Package Outline No.	Specifi- cation Sheet No.
GET2904	40-120					200			Epoxy replacements for 2N2904, 2N2905, 2N2906, 2N2907. GET2904 and GET2905 are lead formed to TO-5 pin circle.	175	45.67
GET2906											
GET2905	-40	-0.4	400	8	50 ¹	110 ¹					
GET2907	100-300					250				45.68	

¹ max switching times @ $I_C=-150mA$, $I_{B1}=I_{B2}=-15mA$